

### 60V N-Channel Enhancement Mode MOSFET

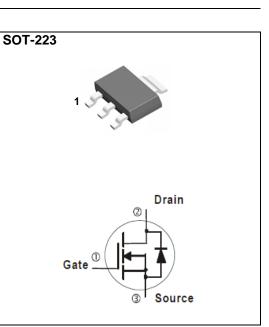
Voltage 60 V Current

#### Features

- $R_{DS(ON)}$ ,  $V_{GS}@10V$ ,  $I_D@5A<75m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@4.5V$ ,  $I_D@3A<90m\Omega$
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

- Case : SOT-223 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.043 ounces, 0.123grams



### **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25<sup>o</sup>C unless otherwise noted)

5 A

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	60	V	
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 20		
Continuous Drain Current (Note 4)	T <sub>A</sub> =25°C	- I <sub>D</sub> -	5	A	
	T <sub>A</sub> =70°C		4		
Pulsed Drain Current (Note 1)		I <sub>DM</sub>	20		
Power Dissipation	T <sub>A</sub> =25°C	PD	3.1	W	
	T <sub>A</sub> =70°C		2		
Operating Junction and Storage Temperature Range		TJ,TSTG	-55~150	°C	
Typical Thermal Resistance					
- Junction to Ambient (Note 4,5)		R <sub>θJA</sub>	40.3	°C/W	

• Limited only By Maximum Junction Temperature



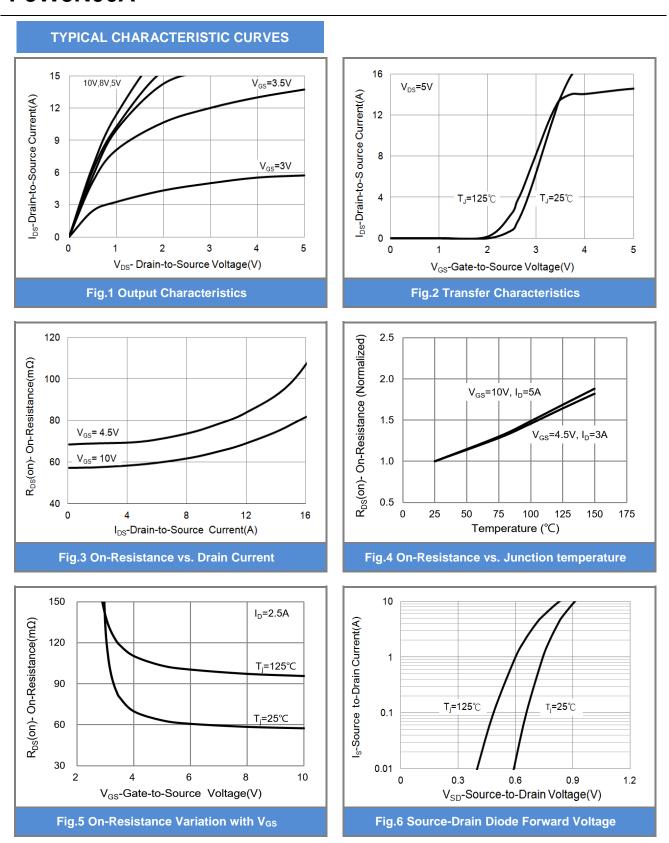
### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static			I	1	1	1	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60	-	-	v	
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1	1.8	2.5		
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	Vgs=10V, Id=5A	-	53	75	mΩ	
		Vgs=4.5V, Id=3A	-	61	90		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V	-	-	1	uA	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA	
Dynamic (Note 6)		·					
Total Gate Charge	Qg	V <sub>DS</sub> =48V, I <sub>D</sub> =3A, V <sub>GS</sub> =10V <sup>(Note 2,3)</sup>	-	9.3	-	nC	
Gate-Source Charge	Qgs		-	2.2	-		
Gate-Drain Charge	Qgd		-	1.9	-		
Input Capacitance	Ciss	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V,	-	509	-	pF	
Output Capacitance	Coss		-	47	-		
Reverse Transfer Capacitance	Crss	f=1MHZ	-	23	-		
Turn-On Delay Time	td(on)	V <sub>DD</sub> =30V, I <sub>D</sub> =3A, V <sub>GS</sub> =10V,	-	3.2	-		
Turn-On Rise Time	tr		-	9.7	-	ns	
Turn-Off Delay Time	td(off)		-	18.5	-		
Turn-Off Fall Time	tf	R <sub>G</sub> =3.3Ω <sup>(Note 2,3)</sup>	-	6.4	-		
Drain-Source Diode							
Maximum Continuous Drain-Source			-	-	5	А	
Diode Forward Current	I <sub>S</sub>						
Diode Forward Voltage	V <sub>SD</sub>	Is=1A, V <sub>GS</sub> =0V	-	0.75	1	V	

NOTES :

- 1. Pulse width</br>
- 2. Essentially independent of operating temperature typical characteristics.
- Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub> =25°C.
- 4. The maximum current rating is package limited.
- 5.  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.







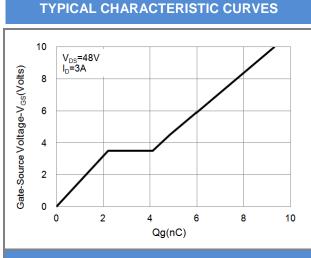


Fig.7 Gate-Charge Characteristics

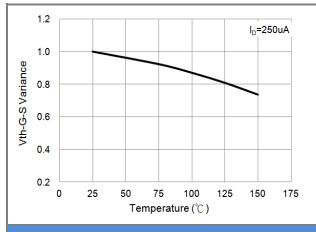
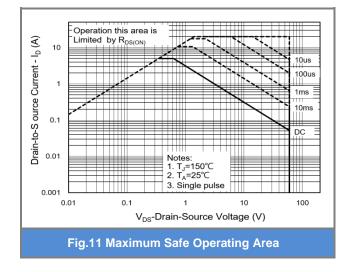
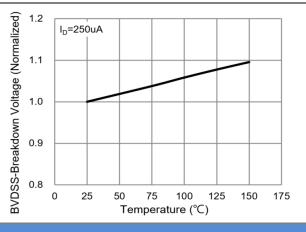


Fig.9 Threshold Voltage Variation with Temperature







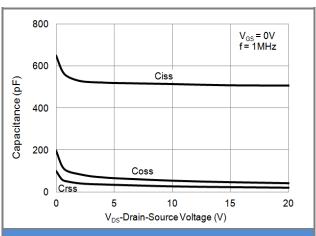
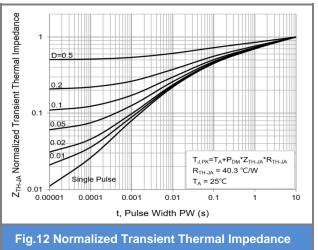


Fig.10 Capacitance vs. Drain-Source Voltage

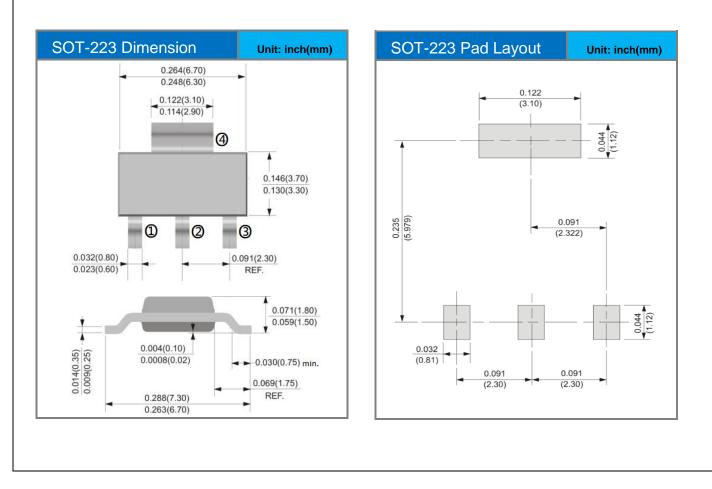




### **Product and Packing Information**

Part No.	Package Type	Packing Type	Marking
PJW5N06A	SOT-223	2,500pcs / 13" reel	W5N06A

### Packaging Information & Mounting Pad Layout





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